

Amendments to the Brief Description of the Drawings:

Please Amend the Specification as follows:

(Currently Amended) ~~FIGS.~~ FIGS. 1A through 1C are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to an embodiment of the present invention.

(Currently Amended) ~~FIGS.~~ FIGS. 2A through 2C are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to the embodiment of the present invention.

(Original) FIG. 3 is a graph showing the relation between mixture ratio and etching selectivity for an etching gas used in the process step of forming a multilayer interconnect according to the embodiment of the present invention, and the relation between the composition of a fluorocarbon gas used as an element of the etching gas and the etching selectivity.

(Original) FIG. 4 is a cross-sectional view illustrating a checking interconnect for checking a multilayer interconnect formed in the method for forming a multilayer interconnect of the embodiment.

(Original) FIGS. 5A through 5C are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to a first known example.

(Currently Amended) FIGS. 6A through ~~6C and 6B~~ cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to the first known example.

(Currently Amended) FIGS. 7A through ~~7C and 7B~~ are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to the first known

example.

(Currently Amended) FIGS. ~~8A through 8C~~ and 8B are cross-sectional views illustrating respective process steps for forming a multilayer interconnect according to a second known example.